Refine Search

Your wildcard search against 10000 terms has yielded the results below.
Your result set for the last L# is incomplete.
The probable cause is use of unlimited truncation. Revise your search strategy to use limited truncation.

Search Results -

Terms	Documents
L3 same test$	23

Database:
US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search: L4

Refine Search | Recall Text | Clear | Interrupt

Search History

DATE: Thursday, December 23, 2004 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR			
L4	L3 same test$	23	L4
L3	L1 near2 device	693	L3
L2	"same adj1 type"	0	L2
L1	(common or identical) adj1 type	28960	L1

END OF SEARCH HISTORY

First Hit Fwd Refs Previous Doc Next Doc Go to Doc#
Generate Collection Print

L4: Entry 15 of 23 File: USPT Jul 10, 1973

DOCUMENT-IDENTIFIER: US 3745460 A
TITLE: METHOD AND APPARATUS FOR DETERMINING THE THERMAL INTERNAL RESISTANCE IN SEMICONDUCTORS OF THE SAME TYPE

Brief Summary Text (12):
According to the method of the present invention, the internal thermal resistance of identical types of semiconductor devices can be measured or correlated in a very short time, i.e., in 50 to 500 ms, depending on the type of the device. Due to the short time required for this test, semiconductor devices of a series can be individually tested in succession. However, a plurality of semiconductor devices of a series can be successively checked in groups or at random if the appropriate number of testing devices and measuring sensors are provided. An arrangement constructed according to an embodiment of the present invention with a thermoelement usable as a temperature sensor for accomplishing the method of the invention for individually testing the semiconductor devices will be explained in detail in the description of the invention provided below.

Previous Doc Next Doc Go to Doc#